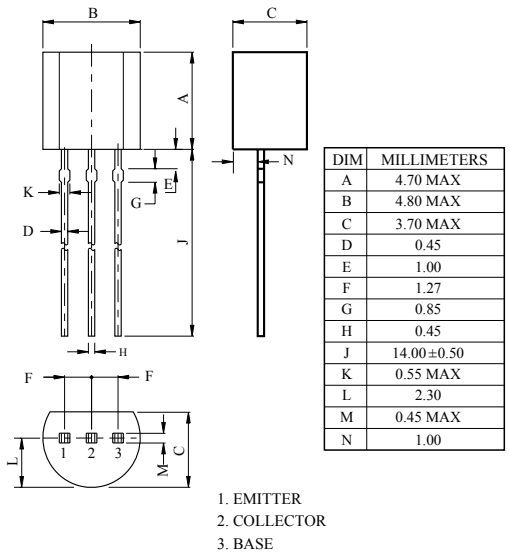
KTB598

EPITAXIAL PLANAR PNP TRANSISTOR

LOW FREQUENCY POWER AMP, CONVERTER
ELECTRONIC GOVERNOR APPLICATIONS

FEATURES

· Low Saturation Voltage
: $V_{CE(sat)}$=-0.3V(Max.) at I_C=-0.5A.
· Complementary to KTD545.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. COLLECTOR
3. BASE

TO-92

MAXIMUM RATING (Ta=25℃)

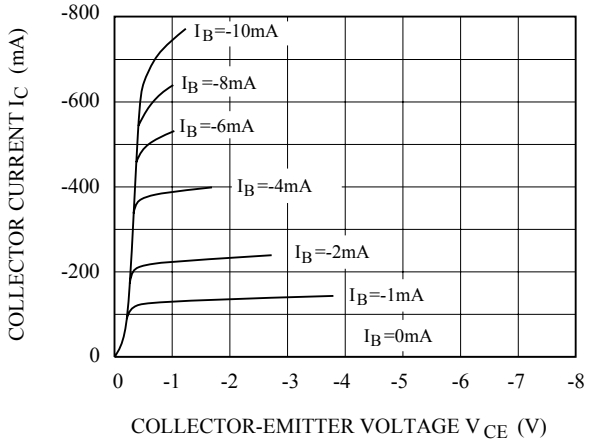
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

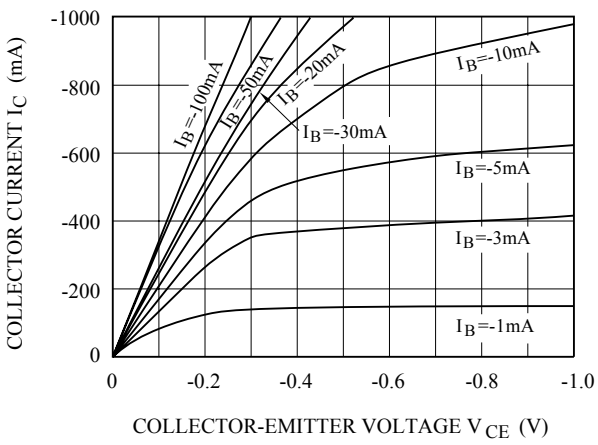
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-20V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=-2V, I_C=-50mA	70	-	400	
	h_{FE}(2)	V_{CE}=-2V, I_C=-1A(Pulse)	30	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-0.15	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA	-	-0.85	-1.2	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-50mA	-	180	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	25	-	pF

Note : h_{FE} Classification O:70～140, Y:120～240, GR:200～400

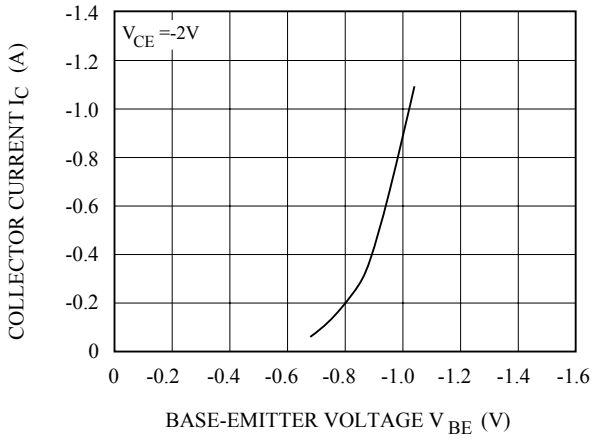
I_C - V_{CE}



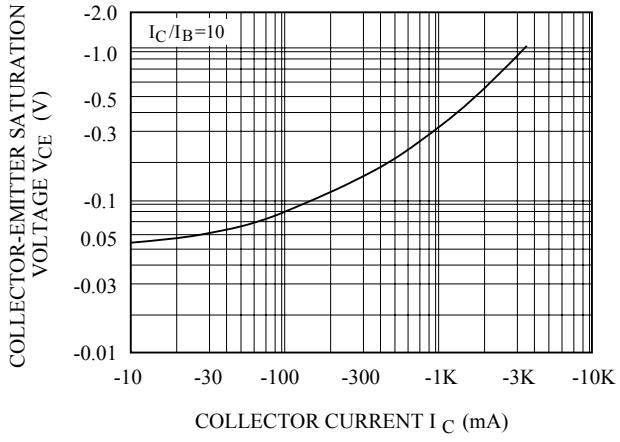
I_C - V_{CE}



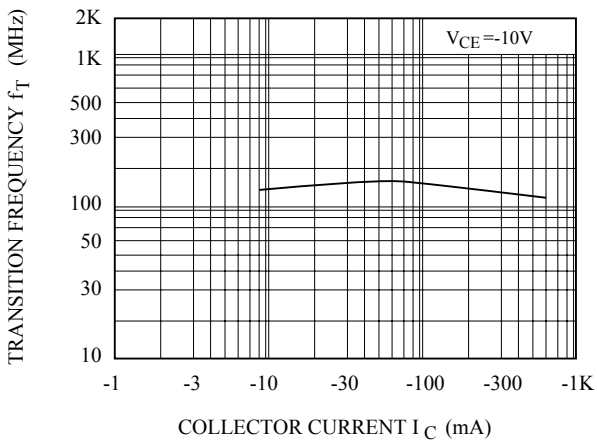
I_C - V_{BE}



$V_{CE(sat)}$ - I_C



f_T - I_C



h_{FE} - I_C

